

July 1999

# FDC642P

# P-Channel 2.5V Specified PowerTrench™ MOSFET

#### **General Description**

This P-Channel 2.5V specified MOSFET is produced using Fairchild's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

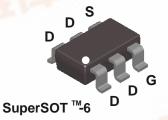
These devices have been designed to offer exceptional power dissipation in a very small footprint for applications where the larger packages are impractical.

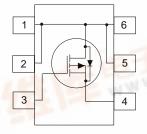
#### **Applications**

- Load switch
- · Battery protection
- Power management

#### **Features**

- -4 A, -20 V.  $R_{DS(ON)} = 0.065 \Omega$  @  $V_{GS} = -4.5 V$   $R_{DS(ON)} = 0.100 \Omega$  @  $V_{GS} = -2.5 V$
- · Fast switching speed.
- · Low gate charge (7.2nC typical).
- High performance trench technology for extremely low R<sub>DS(ON)</sub>.
- SuperSOT™-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).





# Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		-20	V
V <sub>GSS</sub>	Gate-Source Voltage		±8	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1)	-4	A
	Drain Current - Pulsed	(Note 1a)	-20	- W. (1)
P <sub>D</sub>	Power Dissipation for Single Operation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature	re Range	-55 to +150	°C

### **Thermal Characteristics**

R <sub>e</sub> JA	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
R <sub>e</sub> JC	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

Package Outlines and Ordering Information

	- acting a commercial and a commercial a										
	Device Marking	Device	Reel Size	Tape Width	Quantity						
.642		FDC642P	7"	8mm	3000 units						

Symbol	Parameter	Min	Тур	Max	Units	
Off Char	acteristics	,	Į.			
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	-20			V	
ΔBV <sub>DSS</sub> ΔΤ <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = -250 $\mu$ A, Referenced to 25°C		-16		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -16 V, V <sub>GS</sub> = 0 V			-1	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 8 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -8 V, V <sub>DS</sub> = 0 V			-100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-0.4	-0.7	-1.5	V
$\Delta V_{GS(th)}$ $\Delta T_{,J}$	Gate Threshold Voltage Temperature Coefficient	$I_D$ = -250 μA, Referenced to 25°C		2.5		mV/°C
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	$V_{GS} = -4.5 \text{ V}, I_D = -4 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -4 \text{ A}, T_J=125^{\circ}\text{C}$ $V_{GS} = -2.5 \text{ V}, I_D = -3.2 \text{ A}$		0.054 0.076 0.077	0.065 0.105 0.100	Ω
D(on)	On-State Drain Current	V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -5 V	-10			Α
g <sub>FS</sub>	Forward Transconductance	$V_{DS} = -5 \text{ V}, I_{D} = -4 \text{ A}$		9		S
Dvnamic	Characteristics	•	•	•		
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}$		640		pF
Coss	Output Capacitance	f = 1.0 MHz		180		pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1		90		pF
Switchin	g Characteristics (Note 2)					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = -10 V, I <sub>D</sub> = -1 A		11	20	ns
ir	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		19	30	ns
d(off)	Turn-Off Delay Time			26	42	ns
f	Turn-Off Fall Time			35	55	ns
$Q_g$	Total Gate Charge	$V_{DS} = -10 \text{ V}, I_{D} = -4 \text{ A}$		7.2	10	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = -4.5 \text{ V},$		1.7		nC
Q <sub>gd</sub>	Gate-Drain Charge	1		1.6		nC
Drain-Sc	ource Diode Characteristics and	d Maximum Ratings				
ls	Maximum Continuous Drain-Source Did				-1.3	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -1.3 \text{ A}$ (Note 2)		-0.75	-1.2	V

a) 78° C/W when mounted on a 1.0 in² pad of 2 oz. copper.

b) 156° C/W when mounted on a minimum pad of 2 oz.copper.

2. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%

Notes:

1. R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface is determined by the user's board design. of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.

# **Typical Characteristics**

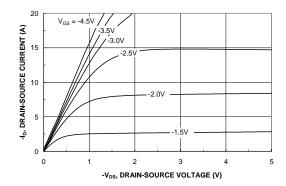


Figure 1. On-Region Characteristics.

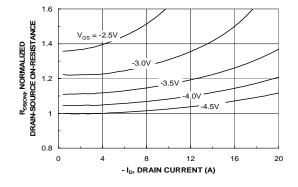


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

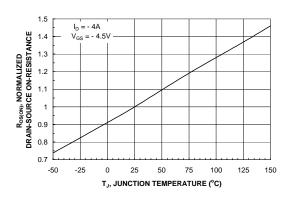


Figure 3. On-Resistance Variation with Temperature.

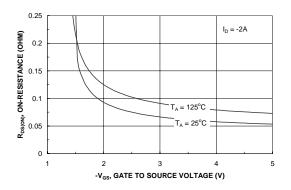


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

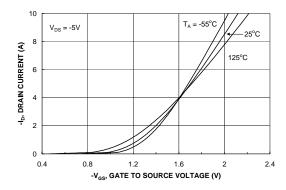


Figure 5. Transfer Characteristics.

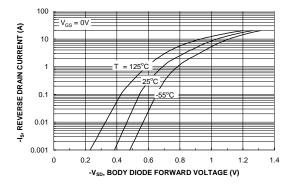
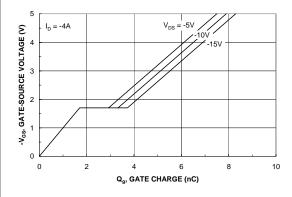


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

# Typical Characteristics (continued)



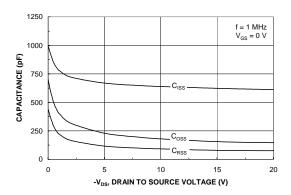
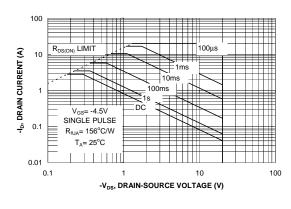


Figure 7. Gate-Charge Characteristics





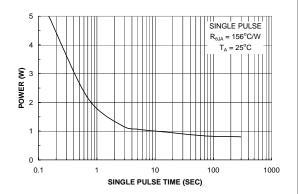


Figure 9. Maximum Safe Operating Area

Figure 10. Single Pulse Maximum Power Dissipation

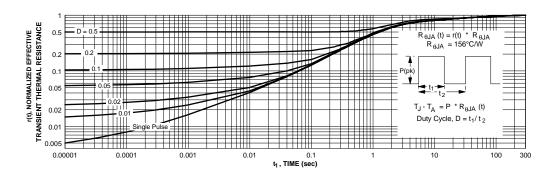
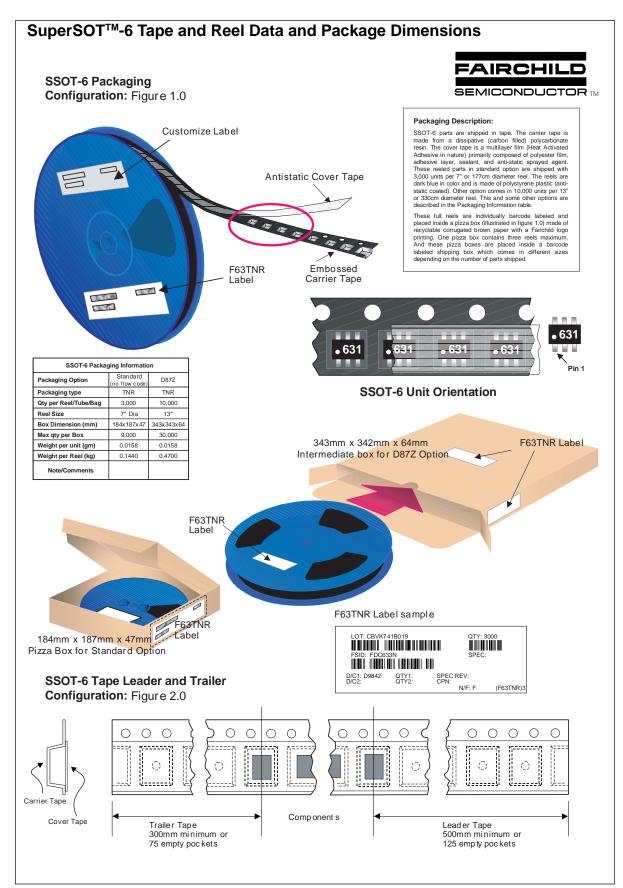


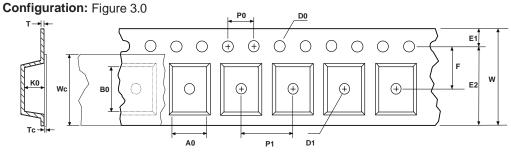
Figure 11. Transient Thermal Response Curve.

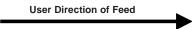
Thermal characterization performed using the conditions described in Note 1b. Transient themal response will change depending on the circuit board design.



# SuperSOT<sup>™</sup>-6 Tape and Reel Data and Package Dimensions, continued

#### **SSOT-6 Embossed Carrier Tape**





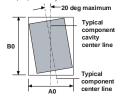
Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-6 (8mm)	3.23 +/-0.10	3.18 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.255 +/-0.150	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).

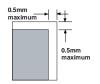


Sketch A (Side or Front Sectional View)
Component Rotation

SSOT-6 Reel Configuration: Figure 4.0



Sketch B (Top View)
Component Rotation



Sketch C (Top View)

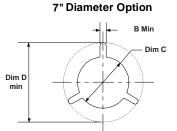
Component lateral movement

# W1 Measured at Hub Dim A See detail AA 13" Diameter Option

Dimensions are in inches and millimeters Reel Option Dim W3 (LSL-USL) Tape Size Dim A Dim B Dim C Dim D Dim N Dim W1 Dim W2 0.059 1.5 512 +0.020/-0.008 13 +0.5/-0.2 2.165 55 0.331 +0.059/-0.000 8.4 +1.5/0 0.311 - 0.429 7.9 - 10.9 8mm 0.059 1.5 512 +0.020/-0.008 13 +0.5/-0.2 0.331 +0.059/-0.000 8.4 +1.5/0 0.567 14.4 0.311 - 0.429 7.9 - 10.9 13" Dia

W2 max Measured at Hub

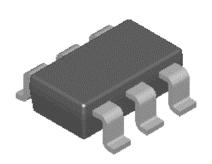
# Dim A See detail AA

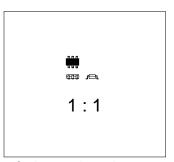


DETAIL AA

# SuperSOT<sup>™</sup>-6 Tape and Reel Data and Package Dimensions, continued

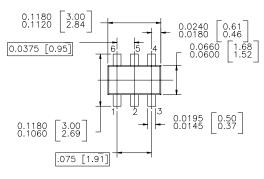
# SuperSOT™-6 (FS PKG Code 31, 33)

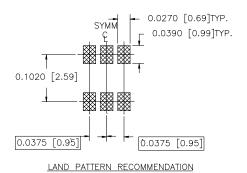




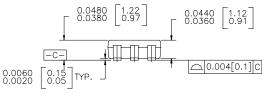
Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

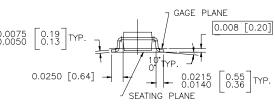
Part Weight per unit (gram): 0.0158





CONTROLLING DIMENSION IS INCH VALUES IN [ ] ARE MILLIMETERS





NOTES: UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH: 150 MICROINCHES 93.81 MICROMETERS) MINIMUM TIN / LEAD (SOLDER) ON COPPER.

2.0 NO JEDEC REGISTRATION AS OF JULY 1996

SUPER SOT 6 LEADS

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 $\begin{array}{lll} \text{FACT Quiet Series}^{\text{TM}} & \text{Quiet Series}^{\text{TM}} \\ \text{FAST}^{\text{\$}} & \text{SuperSOT}^{\text{TM}}\text{-3} \\ \text{FASTr}^{\text{TM}} & \text{SuperSOT}^{\text{TM}}\text{-6} \\ \text{GTO}^{\text{TM}} & \text{SuperSOT}^{\text{TM}}\text{-8} \\ \text{HiSeC}^{\text{TM}} & \text{TinyLogic}^{\text{TM}} \\ \end{array}$ 

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